

MOSFET – N-Channel, POWERTRENCH®

100 V

FDC3612

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

Features

- 2.6 A, 100 V
- $R_{DS(ON)} = 125 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- $R_{DS(ON)} = 135 \text{ m}\Omega @ V_{GS} = 6 \text{ V}$
- High Performance Trench Technology for Extremely Low $R_{DS(ON)}$
- Low Gate Charge (14 nC Typical)
- High Power and Current Handling Capability
- Fast Switching Speed
- This is a Pb-Free Device

Applications

- DC/DC Converter

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

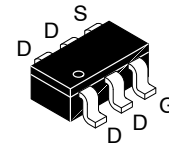
Symbol	Parameter	Ratings	Unit
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	Continuous (Note 1a)	2.6
		Pulsed	20
E_{AS}	Single Pulse Avalanche Energy (Note 3)	37	mJ
P_D	Maximum Power Dissipation	(Note 1a)	1.6
		(Note 1b)	0.8
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

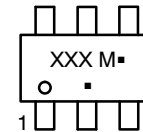
Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	30	$^\circ\text{C/W}$

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
100 V	125 m Ω @ 10 V	2.6 A
	135 m Ω @ 6 V	



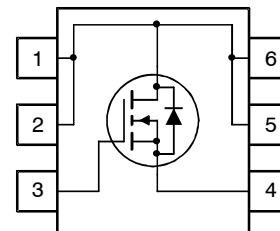
TSOT23 6-Lead
(SUPERSOT™ -6)
CASE 419BL

MARKING DIAGRAM



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PINOUT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDC3612

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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DRAIN-SOURCE AVALANCHE RATINGS (Note 2)

W _{DSS}	Drain-Source Avalanche Energy	Single Pulse, V _{DD} = 50 V, I _D = 2.6 A	–	–	90	mJ
I _{AR}	Drain-Source Avalanche Current		–	–	2.6	A

OFF CHARACTERISTICS

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	100	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	99	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V	–	–	10	μA
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V	–	–	100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = –20 V, V _{DS} = 0 V	–	–	–100	nA

ON CHARACTERISTICS (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	2.3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	–6	–	mV/°C
R _{DS(on)}	Static Drain-Source On Resistance	V _{GS} = 10 V, I _D = 2.6 A V _{GS} = 6 V, I _D = 2.5 A V _{GS} = 10 V, I _D = 2.6 A, T _J = 125°C	– – –	86 91 157	125 135 240	mΩ
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	10	–	–	A
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 2.6 A	–	10	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 50 V, V _{GS} = 0 V, f = 1.0 MHz	–	660	–	pF
C _{oss}	Output Capacitance		–	55	–	pF
C _{rss}	Reverse Transfer Capacitance		–	40	–	pF
R _g	Gate Resistance		0.1	1.4	3.0	Ω

SWITCHING CHARACTERISTICS (Note 2)

t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	–	6	11	ns
t _r	Turn-On Rise Time		–	3.5	7	ns
t _{d(off)}	Turn-Off Delay Time		–	23	37	ns
t _f	Turn-Off Fall Time		–	3.7	7.4	ns
Q _g	Total Gate Charge	V _{DS} = 50 V, I _D = 2.6 A, V _{GS} = 10 V	–	14	20	nC
Q _{gs}	Gate-Source Charge		–	2.3	–	nC
Q _{gd}	Gate-Drain Charge		–	3.6	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain-Source Diode Forward Current		–	–	1.3	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.3 A (Note 2)	–	0.76	1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = 2.6 A, dI _F /dt = 100 A/μs (Note 2)	–	31	–	ns
Q _{rr}	Diode Reverse Recovery Charge	I _F = 2.6 A, dI _F /dt = 100 A/μs (Note 2)	–	56	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.
 - 78 °C/W when mounted on a 1in² pad of 2oz copper on FR-4 board
 - 156 °C/W when mounted on a minimum pad
- Pulse Test: Pulse Width ≤ 300 μs, Duty cycle ≤ 2.0 %
- E_{AS} of 37 mJ is based on starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 5 A, V_{DD} = 100 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 11 A.

TYPICAL CHARACTERISTICS

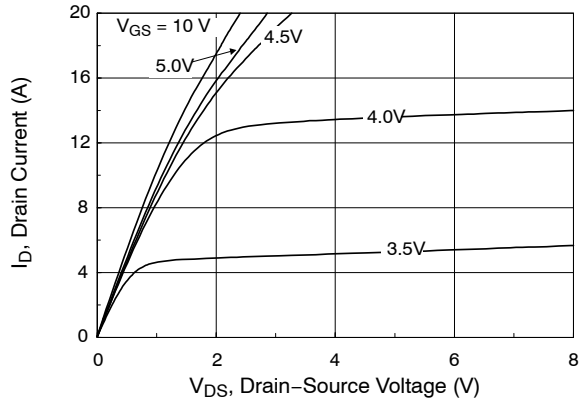


Figure 1. On-Region Characteristics

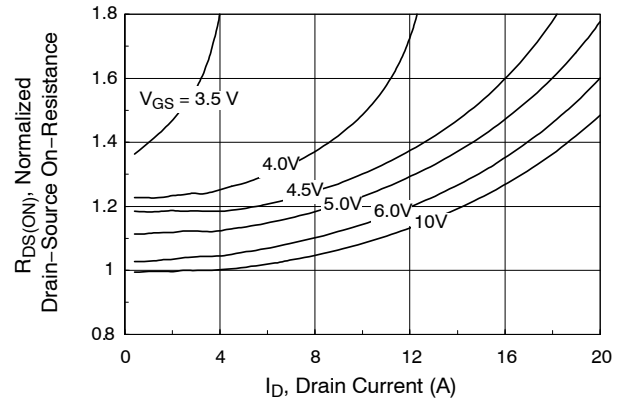


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

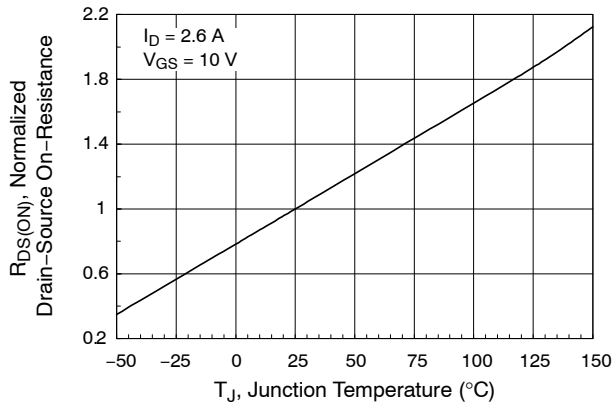


Figure 3. On-Resistance Variation with Temperature

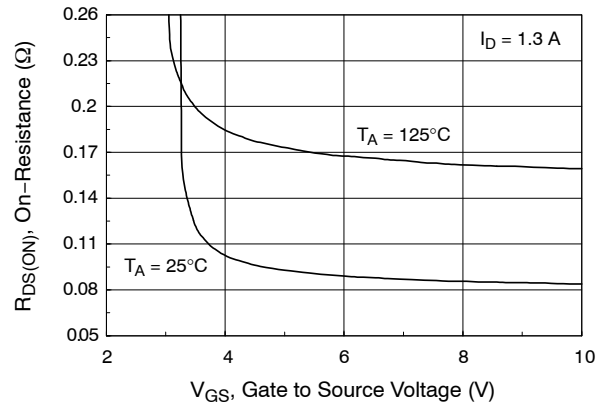


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

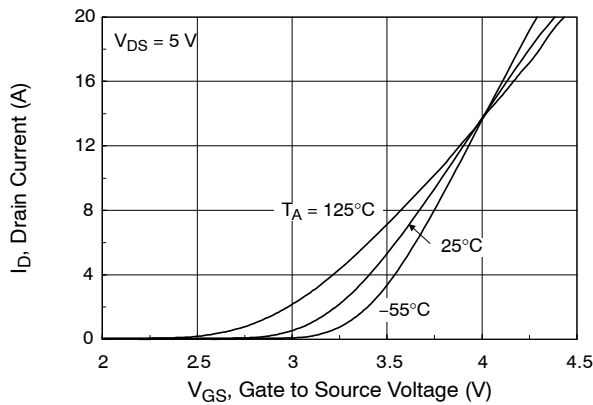


Figure 5. Transfer Characteristics

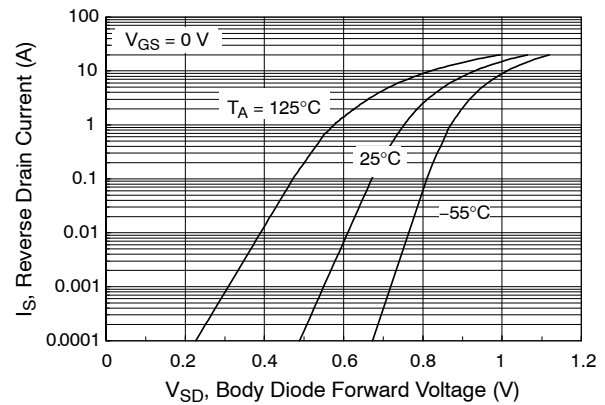


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL ELECTRICAL CHARACTERISTICS (continued)

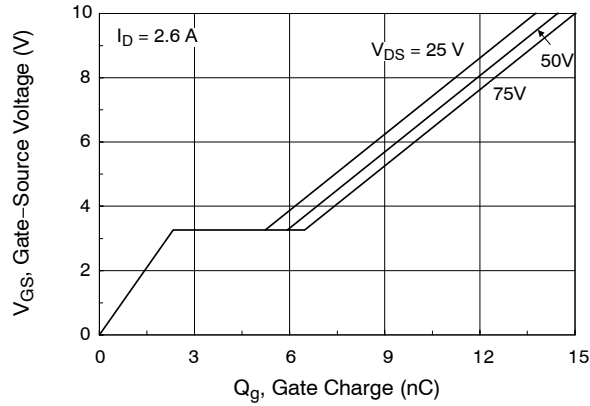


Figure 7. Gate Charge Characteristics

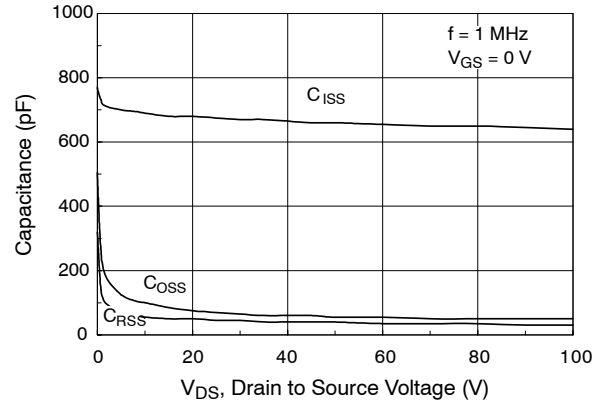


Figure 8. Capacitance Characteristics

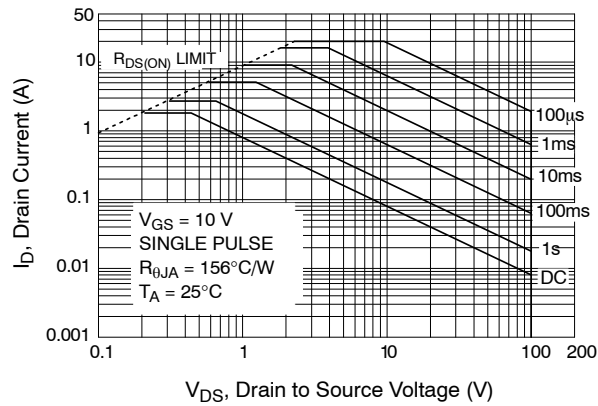


Figure 9. Maximum Safe Operating Area

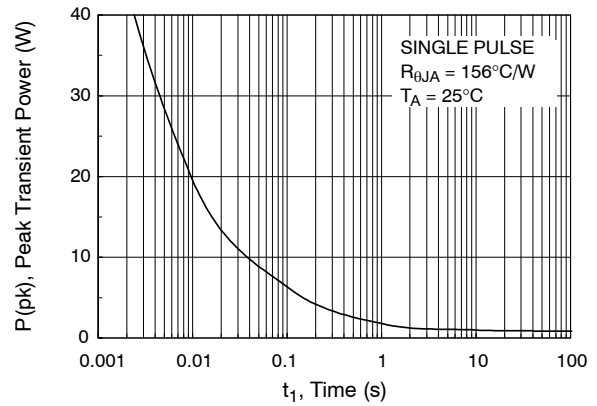


Figure 10. Single Pulse Maximum Power Dissipation

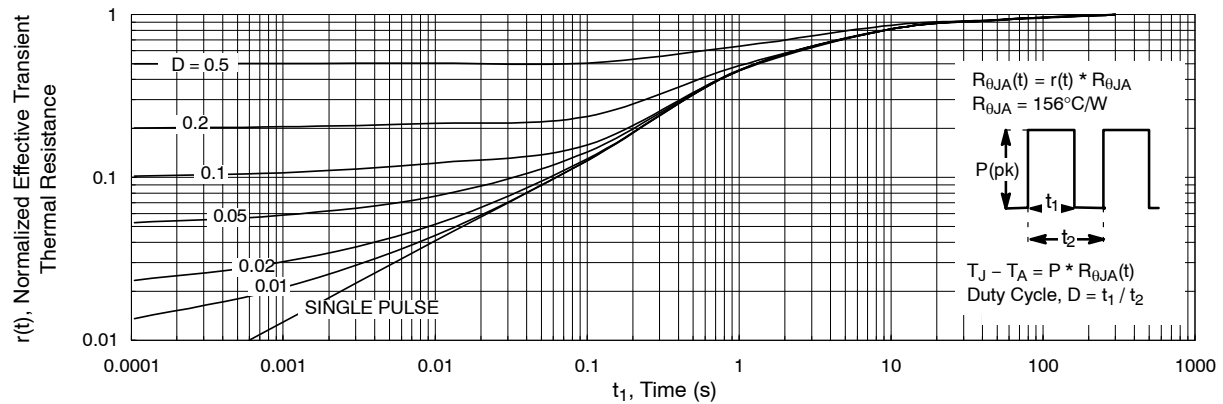


Figure 11. Transient Thermal Response Curve

(Note: Thermal characterization performed using the conditions described in Note 1b.

Transient thermal response will change depending on the circuit board design.)

FDC3612

ORDERING INFORMATION

Device	Device Marking	Package Type	Shipping [†]
FDC3612	.362	TSOT-23-6 (Pb-free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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SCALE 2:1

TSOT23 6-Lead
CASE 419BL
ISSUE A

DATE 31 AUG 2020



TOP VIEW



FRONT VIEW



DETAIL A



SIDE VIEW

SYMM


LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE ON SEMICONDUCTOR
SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25MM PER END. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.70	0.85	1.00
A3	0.25 BSC		
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.80	2.95	3.10
d	0.30 REF		
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.95 BSC		
e1	1.90 BSC		
L1	0.60 REF		
L2	0.20	0.40	0.60
Θ	0°	—	10°

**GENERIC
MARKING DIAGRAM***


XXX = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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